N-Channel Enhancement Mode Field Effect Transistor

General Description

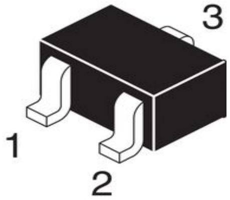
Product Summary		
V_{DSS}	I_D	$R_{DS(ON)}$(mΩ)TYP
20V	0.65A	260 @ VGS= 4.5V
	0.55A	320 @ VGS= 2.5V

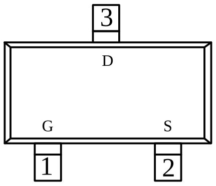
Features

- Super high dense cell design for low $R_{DS(ON)}$
- Rugged and reliable
- Simple drive requirement
- SOT-23-3L/B package

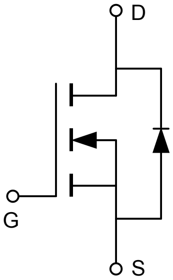
Package

- **SOT-23-3B/ SOT-23-3L**





SOT-23-3B/SOT-23-3L
(Top View)



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PN2308	-55°C to +150℃	SOT-23-3L/B	3000

Absolute Maximum Ratings

(TA=25℃ unless otherwise noted)

parameter		symbol	limit	unit
Drain-source voltage		V_{DSS}	20	V
Gate-source voltage		V_{GSS}	±12	V
Coutinuous drain current (Tj=150℃)	TA=25℃	I_D	0.65	A
	TA=80℃		0.45	A
Pulsed drain current		I_{DM}	1.0	A
Drain-source Diode forward current		Is	0.3	A
Power dissipation	TA=25℃	P_D	0.27	W
	TA=70℃		0.16	
Operating junction Temperature range		T_j	-55—150	℃